

Emanuele Rimini

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248
papers

4,834
citations

33
h-index

58
g-index

257
ext. papers

5,041
ext. citations

2.9
avg. IF

4.85
L-index

#	Paper	IF	Citations
248	A melting model for pulsing-laser annealing of implanted semiconductors. <i>Journal of Applied Physics</i> , 1979 , 50, 788-797	2.5	362
247	Ion irradiation and defect formation in single layer graphene. <i>Carbon</i> , 2009 , 47, 3201-3207	10.4	186
246	Ion-beam-induced epitaxial crystallization and amorphization in silicon. <i>Materials Science and Engineering Reports</i> , 1990 , 5, 319-379		186
245	Amorphous-to-crystal transition of nitrogen- and oxygen-doped Ge ₂ Sb ₂ Te ₅ films studied by in situ resistance measurements. <i>Applied Physics Letters</i> , 2004 , 85, 3044-3046	3.4	180
244	Voids in Silicon by He Implantation: From Basic to Applications. <i>Journal of Materials Research</i> , 2000 , 15, 1449-1477	2.5	130
243	Arsenic diffusion in silicon melted by high-power nanosecond laser pulsing. <i>Applied Physics Letters</i> , 1978 , 33, 137-140	3.4	121
242	Screening length and quantum capacitance in graphene by scanning probe microscopy. <i>Nano Letters</i> , 2009 , 9, 23-9	11.5	95
241	Mapping the density of scattering centers limiting the electron mean free path in graphene. <i>Nano Letters</i> , 2011 , 11, 4612-8	11.5	84
240	Segregation Effects in Cu-Implanted Si after Laser-Pulse Melting. <i>Physical Review Letters</i> , 1978 , 41, 1246-1249	7.7	77
239	Metal-Insulator Transition Driven by Vacancy Ordering in GeSbTe Phase Change Materials. <i>Scientific Reports</i> , 2016 , 6, 23843	4.9	77
238	Dechanneling by dislocations in ion-implanted Al. <i>Physical Review B</i> , 1978 , 18, 2078-2096	3.3	76
237	Dependence of trapping and segregation of indium in silicon on the velocity of the liquid-solid interface. <i>Applied Physics Letters</i> , 1980 , 37, 912-914	3.4	75
236	Crystal nucleation and growth processes in Ge ₂ Sb ₂ Te ₅ . <i>Applied Physics Letters</i> , 2004 , 84, 4448-4450	3.4	70
235	Silicon planar technology for single-photon optical detectors. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 918-925	2.9	67
234	Solute trapping by moving interface in ion-implanted silicon. <i>Applied Physics Letters</i> , 1980 , 37, 719-722	3.4	66
233	Channeling measurements in As-doped Si. <i>Journal of Applied Physics</i> , 1972 , 43, 3425-3431	2.5	66
232	Phenomenological description of ion-beam-induced epitaxial crystallization of amorphous silicon. <i>Physical Review B</i> , 1990 , 41, 5235-5242	3.3	64

231	Crystallization and phase separation in Ge _{2+x} Sb ₂ Te ₅ thin films. <i>Journal of Applied Physics</i> , 2003 , 94, 4409-4413	62
230	Temperature and Energy Dependence of Proton Dechanneling in Silicon. <i>Physical Review B</i> , 1971 , 3, 2169-2179	62
229	Supersaturated solid solutions after solid phase epitaxial growth in Bi-implanted silicon. <i>Applied Physics Letters</i> , 1980 , 37, 170-172	3-4 55
228	Role of graphene/substrate interface on the local transport properties of the two-dimensional electron gas. <i>Applied Physics Letters</i> , 2010 , 97, 132101	3-4 54
227	Lattice location of Te in laser-annealed Te-implanted silicon. <i>Journal of Applied Physics</i> , 1978 , 49, 2569	2-5 54
226	Structure of crystallized layers by laser annealing of <100> and <111> self-implanted silicon samples. <i>Applied Physics Berlin</i> , 1978 , 15, 365-369	51
225	Ion irradiation-induced local structural changes in amorphous Ge ₂ Sb ₂ Te ₅ thin film. <i>Applied Physics Letters</i> , 2008 , 92, 241925	3-4 49
224	Grain size dependence in a self-implanted silicon layer on laser irradiation energy density. <i>Applied Physics Letters</i> , 1978 , 32, 824-826	3-4 47
223	Ion-beam-assisted growth of doped Si layers. <i>Journal of Materials Research</i> , 1988 , 3, 1212-1217	2-5 44
222	Amorphous-polycrystal transition induced by laser pulse in self-ion implanted silicon. <i>Applied Physics Berlin</i> , 1977 , 14, 189-191	43
221	Evidence for small interstitial clusters as the origin of photoluminescence W band in ion-implanted silicon. <i>Applied Physics Letters</i> , 2001 , 78, 291-293	3-4 39
220	Time-resolved temperature measurement of pulsed laser irradiated germanium by thin-film thermocouple. <i>Applied Physics Letters</i> , 1984 , 45, 398-400	3-4 38
219	Determination of concentration profile in thin metallic films: Applications and limitations of He ⁺ backscattering. <i>Thin Solid Films</i> , 1975 , 25, 431-440	2-2 37
218	Channeling analysis of stacking defects in epitaxial Si layers. <i>Nuclear Instruments & Methods</i> , 1978 , 149, 371-376	37
217	Depth profile studies of extended defects induced by ion implantation in Si and Al. <i>Radiation Effects</i> , 1980 , 49, 75-79	35
216	Surface structure changes by laser pulses in silicon. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1977 , 63, 351-354	2-3 35
215	Amorphous-crystal silicon interfaces: structure and movement under ion beam irradiation. <i>Applied Surface Science</i> , 1992 , 56-58, 577-588	6-7 33
214	Chemical and structural arrangement of the trigonal phase in GeSbTe thin films. <i>Nanotechnology</i> , 2017 , 28, 065706	3-4 32

213	Laser annealing of silicon. <i>Materials Chemistry and Physics</i> , 1996 , 46, 169-177	4.4	32
212	Irradiation damage in graphene on SiO ₂ probed by local mobility measurements. <i>Applied Physics Letters</i> , 2009 , 95, 263109	3.4	30
211	Electrical characterization of ultra-shallow junctions formed by diffusion from a CoSi/sub 2/ layer. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 526-534	2.9	30
210	Ion-induced annealing and amorphization of isolated damage clusters in Si. <i>Applied Physics Letters</i> , 1990 , 56, 2622-2624	3.4	30
209	Channeling in Si Overlaid with Al and Au Films. <i>Physical Review B</i> , 1972 , 6, 718-728	3.3	30
208	Beam Effects in the Analysis of As-Doped Silicon by Channeling Measurements. <i>Applied Physics Letters</i> , 1972 , 20, 237-239	3.4	30
207	Amorphous-Crystal Phase Transitions in Ge _x Te _{1-x} Alloys. <i>Journal of the Electrochemical Society</i> , 2011 , 159, H130-H139	3.9	29
206	Ion-assisted recrystallization of amorphous silicon. <i>Applied Surface Science</i> , 1989 , 43, 178-186	6.7	28
205	Ion-induced epitaxial growth of chemical vapor deposited Si layers. <i>Applied Physics Letters</i> , 1988 , 52, 712-714	3.4	28
204	Amorphous thickness dependence in the transition to single crystal induced by laser pulse. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1978 , 65, 430-432	2.3	28
203	Effect of O:Er concentration ratio on the structural, electrical, and optical properties of Si:Er:O layers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2000 , 88, 4091	2.5	26
202	Depth distribution of B implanted in Si after excimer laser irradiation. <i>Applied Physics Letters</i> , 2005 , 86, 051909	3.4	25
201	Diffusion and outdiffusion of aluminium implanted into silicon. <i>Semiconductor Science and Technology</i> , 1993 , 8, 488-494	1.8	25
200	Influence of a thin interfacial oxide layer on the ion beam assisted epitaxial crystallization of deposited Si. <i>Applied Physics Letters</i> , 1988 , 53, 2605-2607	3.4	25
199	Epitaxial NiSi ₂ formation by pulsed laser irradiation of thin Ni layers deposited on Si substrates. <i>Applied Physics Letters</i> , 1983 , 43, 244-246	3.4	25
198	Laser pulse annealing of ion-implanted GaAs. <i>Journal of Applied Physics</i> , 1980 , 51, 295-298	2.5	25
197	Crystallization of sputtered-deposited and ion implanted amorphous Ge ₂ Sb ₂ Te ₅ thin films. <i>Journal of Applied Physics</i> , 2009 , 105, 123502	2.5	24
196	Quantitative determination of the clustered silicon concentration in substoichiometric silicon oxide layer. <i>Applied Physics Letters</i> , 2005 , 87, 044102	3.4	24

195	Implants of 1550 MeV Boron ions into silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1989 , 2, 69-73	3.1	24
194	Single photon avalanche photodiodes arrays. <i>Sensors and Actuators A: Physical</i> , 2007 , 138, 306-312	3.9	23
193	Evidence of a replacement reaction between ion implanted substitutional Tl dopants and interstitial Si atoms. <i>Radiation Effects</i> , 1969 , 1, 249-256		23
192	Arrays of Geiger mode avalanche photodiodes. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1633-1635	2.2	22
191	Pseudoepitaxial transrotational structures in 14 nm-thick NiSi layers on [001] silicon. <i>Acta Crystallographica Section B: Structural Science</i> , 2005 , 61, 486-91		22
190	Low-temperature reordering in partially amorphized Si crystals. <i>Applied Physics Letters</i> , 1990 , 57, 768-770	3.4	22
189	Rapid thermal oxidation of epitaxial SiGe thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 269-273	3.1	21
188	Ion-beam-induced epitaxial crystallization and amorphization in silicon. <i>Materials Science and Engineering Reports</i> , 1990 , 5, 321-379		21
187	Ion beam and temperature annealing during high dose implants. <i>Applied Physics Letters</i> , 1985 , 47, 138-140	3.4	21
186	Effect of ion energy on the implantation products of benzene. <i>Chemical Physics Letters</i> , 1981 , 78, 207-211	1.5	21
185	Structure transitions in amorphous silicon under laser irradiation. <i>Journal of Applied Physics</i> , 1979 , 50, 259-265	2.5	21
184	Role of the internal strain on the incomplete SiBiO ₂ phase separation in substoichiometric silicon oxide films. <i>Applied Physics Letters</i> , 2007 , 90, 183101	3.4	20
183	Effect of the linewidth reduction on the characteristic time spread in C49/C54 phase transition. <i>Applied Physics Letters</i> , 1998 , 73, 3863-3865	3.4	20
182	Thermal stability of cobalt silicide stripes on Si (001). <i>Journal of Applied Physics</i> , 1999 , 86, 3089-3095	2.5	20
181	Ag-Assisted Chemical Etching of (100) and (111) n-Type Silicon Substrates by Varying the Amount of Deposited Metal. <i>Journal of the Electrochemical Society</i> , 2012 , 159, D521-D525	3.9	19
180	Nucleation and grain growth in as deposited and ion implanted GeTe thin films. <i>Journal of Non-Crystalline Solids</i> , 2011 , 357, 2197-2201	3.9	19
179	Crystallization of ion amorphized Ge ₂ Sb ₂ Te ₅ thin films in presence of cubic or hexagonal phase. <i>Journal of Applied Physics</i> , 2010 , 107, 113521	2.5	19
178	High-energy channeling implants of phosphorus along the silicon. <i>Physical Review B</i> , 1991 , 44, 10568-10577	3.7	19

177	Amorphous-fcc transition in Ge ₂ Sb ₂ Te ₅ . <i>Microelectronic Engineering</i> , 2010 , 87, 294-300	2.5	18
176	Critical nickel thickness to form silicide transrotational structures on [001] silicon. <i>Applied Physics Letters</i> , 2006 , 89, 102105	3.4	18
175	Nucleation and growth of C54 grains into C49 TiSi ₂ thin films monitored by micro-Raman imaging. <i>Journal of Applied Physics</i> , 2000 , 88, 7013-7019	2.5	18
174	Al-O complex formation in ion implanted Czochralski and floating-zone Si substrates. <i>Applied Physics Letters</i> , 1993 , 62, 393-395	3.4	18
173	Channeling implants of B ions into silicon surfaces. <i>Radiation Effects and Defects in Solids</i> , 1991 , 116, 211-217	0.9	17
172	Channeling effect study of deuteron induced damage in Si and Ge crystals. <i>Applied Physics Letters</i> , 1975 , 26, 424-426	3.4	17
171	Polymorphism of Amorphous Ge ₂ Sb ₂ Te ₅ Probed by EXAFS and Raman Spectroscopy. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H480		16
170	Channeling implants in silicon crystals. <i>Materials Chemistry and Physics</i> , 1994 , 38, 105-130	4.4	16
169	Phase formation in Au-Al and Cu-Al thin-film systems under ion beam bombardment. <i>Journal of Applied Physics</i> , 1984 , 55, 3322-3326	2.5	16
168	Melting dynamics of NiSi ₂ /Si under pulsed laser irradiation. <i>Physical Review B</i> , 1987 , 35, 5117-5122	3.3	15
167	Fundamental optical properties of heavily-boron-doped silicon. <i>Physical Review B</i> , 1987 , 36, 9563-9568	3.3	15
166	Optical reflectivity of ion-implanted amorphous GaAs. <i>Applied Physics Letters</i> , 1978 , 33, 632-634	3.4	15
165	Low temperature interdiffusion in copper-gold thin films analysed by helium back-scattering. <i>Thin Solid Films</i> , 1973 , 19, 339-348	2.2	15
164	Voids in silicon power devices. <i>Solid-State Electronics</i> , 1998 , 42, 2295-2301	1.7	14
163	Al-O interactions in ion-implanted crystalline silicon. <i>Journal of Applied Physics</i> , 1994 , 76, 2070-2077	2.5	14
162	Precipitation of arsenic diffused into silicon from a TiSi ₂ source. <i>Journal of Applied Physics</i> , 1991 , 69, 7262-7271		14
161	Kinetic and structural study of the epitaxial realignment of polycrystalline Si films. <i>Journal of Applied Physics</i> , 1992 , 71, 638-647	2.5	14
160	Boron implants in silicon at tilt angles of 0 degrees and 7 degrees. <i>Semiconductor Science and Technology</i> , 1990 , 5, 1007-1012	1.8	14

159	Ion beam annealing during high current density implants of phosphorus into silicon. <i>Journal of Applied Physics</i> , 1986 , 59, 4038-4042	2.5	14
158	Optical study of self-annealing in high-current arsenic-implanted silicon. <i>Journal of Applied Physics</i> , 1985 , 58, 2773-2776	2.5	14
157	Experimental investigation of the amorphous silicon melting temperature by fast heating processes. <i>Journal of Applied Physics</i> , 1982 , 53, 8730-8733	2.5	14
156	Ion mass effect in channelling. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1970 , 31, 214-215	2.3	14
155	Amorphous to fcc-polycrystal transition in Ge ₂ Sb ₂ Te ₅ thin films studied by electrical measurements: Data analysis and comparison with direct microscopy observations. <i>Journal of Applied Physics</i> , 2009 , 105, 083546	2.5	13
154	Selective diffusion of gold nanodots on nanopatterned substrates realized by self-assembly of diblock copolymers. <i>Journal of Materials Research</i> , 2011 , 26, 240-246	2.5	13
153	Peculiar aspects of nanocrystal memory cells: data and extrapolations. <i>IEEE Nanotechnology Magazine</i> , 2003 , 2, 319-323	2.6	13
152	Direct measurement of the growth rate during the C49 to C54 transformation in TiSi ₂ : Activation energy. <i>Journal of Applied Physics</i> , 2002 , 92, 627-628	2.5	13
151	Roughness of thermal oxide layers grown on ion implanted silicon wafers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 619		13
150	Epitaxial silicide formation by multi-shot irradiation of Ni thin films on Si with Nd laser. <i>Journal of Applied Physics</i> , 1985 , 57, 4560-4565	2.5	13
149	Pulsed-laser annealing of implanted layers in GaAs. <i>Applied Physics Letters</i> , 1979 , 34, 597-599	3.4	13
148	Investigation of Ag-Assisted Chemical Etching on (100) and (111) Contiguous Silicon Surfaces. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, P405-P412	2	12
147	Low temperature formation and evolution of a 10 nm amorphous Ni ₃ Si layer on [001] silicon studied by in situ transmission electron microscopy. <i>Journal of Applied Physics</i> , 2009 , 105, 093506	2.5	12
146	Crosstalk Characterization in Geiger-Mode Avalanche Photodiode Arrays. <i>IEEE Electron Device Letters</i> , 2008 , 29, 218-220	4.4	12
145	Structural characterization of Ni ₂ Si pseudoepitaxial transrotational structures on [001] Si. <i>Acta Crystallographica Section B: Structural Science</i> , 2006 , 62, 729-36		12
144	Formation and annealing of defects during high-temperature processing of ion-implanted epitaxial silicon: the role of dopant implants. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000 , 71, 186-191	3.1	12
143	Al-Based Precipitate Evolution during High Temperature Annealing of Al Implanted in Si. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 2313-2318	3.9	12
142	Chemical effects of ion implantation on solid benzene. <i>Chemical Physics Letters</i> , 1980 , 70, 392-396	2.5	12

141	Pulsed laser irradiation of lead-implanted single-crystal copper films. <i>Applied Physics Letters</i> , 1980 , 37, 481-483	3.4	12
140	Laser induced single-crystal transition in polycrystalline silicon. <i>Applied Physics Berlin</i> , 1978 , 17, 111-113		12
139	Laser pulse energy dependence of annealing in ion implanted Si and GaAs semiconductors. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1978 , 65, 153-155	2.3	12
138	Quantitative depth distribution of dislocations by planar channeling. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1978 , 68, 244-246	2.3	12
137	Scattering in an Amorphous Layer Measured by Dechanneling. <i>Physical Review B</i> , 1973 , 8, 1811-1821	3.3	12
136	Local Order and Crystallization of Laser Quenched and Ion Implanted Amorphous Ge _x Te _{1-x} Thin Films. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H317		11
135	Arsenic redistribution at the SiO ₂ /Si interface during oxidation of implanted silicon. <i>Physical Review B</i> , 1998 , 58, 10990-10999	3.3	11
134	Surface accumulation of Te atoms in laser melted Te-implanted silicon. <i>Journal of Applied Physics</i> , 1980 , 51, 3968-3970	2.5	11
133	Laser annealing of Pb-implanted silicon. <i>Physica Status Solidi A</i> , 1978 , 47, 533-538		11
132	Tilting angle dependence of Rutherford backscattering: Uniformity of near surface layers. <i>Nuclear Instruments & Methods</i> , 1978 , 149, 229-233		11
131	Atomic diffusion in laser irradiated Ge rich GeSbTe thin films for phase change memory applications. <i>Journal Physics D: Applied Physics</i> , 2018 , 51, 145103	3	10
130	Lateral homogeneity of the electronic properties in pristine and ion-irradiated graphene probed by scanning capacitance spectroscopy. <i>Nanoscale Research Letters</i> , 2011 , 6, 109	5	10
129	Thermal oxidation of Si (001) single crystal implanted with Ge ions. <i>Journal of Applied Physics</i> , 2002 , 91, 6754	2.5	10
128	Beam-induced lattice disorder in channeling experiments on Si and Ge. <i>Applied Physics Letters</i> , 1972 , 21, 425-427	3.4	10
127	Formation, Morphology, and Optical Properties of Electroless Deposited Gold Nanoparticles on 3C-SiC. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 4304-4311	3.8	9
126	Electroless Deposition of Silver Investigated with Rutherford Backscattering and Electron Microscopy. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P235-P242	2	9
125	Investigation of graphene/SiC interface by nanoscale electrical characterization. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 912-915	1.3	9
124	Nucleation and growth of NiSi from Ni ₂ Si transrotational domains. <i>Applied Physics Letters</i> , 2007 , 90, 053507		9

123	Lattice location and thermal evolution of small B complexes in crystalline Si. <i>Applied Physics Letters</i> , 2005 , 87, 201905	3.4	9
122	Effects of N-induced heterogeneous nucleation and growth of cavities at the CoSi ₂ /polycrystalline Silicon interface. <i>Applied Physics Letters</i> , 2002 , 81, 55-57	3.4	9
121	Photoluminescence and structural studies on extended defect evolution during high-temperature processing of ion-implanted epitaxial silicon. <i>Journal of Applied Physics</i> , 2001 , 89, 4310-4317	2.5	9
120	Two-dimensional distributions of ions implanted in channeling and random directions of Si single crystals. <i>Journal of Applied Physics</i> , 1993 , 74, 2370-2377	2.5	9
119	Evidence of interfacial melting during pulsed laser irradiation of Ni ₂ Si on Si. <i>Applied Physics Letters</i> , 1987 , 51, 649-651	3.4	9
118	Influence of implanted dose on the recrystallization of Si amorphous layer. <i>Applied Physics Letters</i> , 1975 , 26, 154-155	3.4	9
117	Distribution across the channel of defects induced by nitrogen bombardment in silicon. <i>Applied Physics Letters</i> , 1976 , 28, 9-11	3.4	9
116	Single-crystal heteroepitaxial growth of Pb _x Sn _{1-x} Te films on germanium substrates by r.f. sputtering. <i>Thin Solid Films</i> , 1976 , 33, 135-148	2.2	9
115	Radial distribution of ion-induced defects determined by channeling measurements. <i>Nuclear Instruments & Methods</i> , 1976 , 132, 237-240		9
114	Reduced electronic scattering in dechannelling. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1970 , 33, 433-434	2.3	9
113	Mechanical properties of amorphous Ge ₂ Sb ₂ Te ₅ thin layers. <i>Surface and Coatings Technology</i> , 2018 , 355, 227-233	4.4	8
112	Transport Properties of Graphene with Nanoscale Lateral Resolution. <i>Nanoscience and Technology</i> , 2011 , 247-285	0.6	8
111	Test of scintillator readout with single photon avalanche photodiodes. <i>IEEE Transactions on Nuclear Science</i> , 2005 , 52, 3040-3046	1.7	8
110	Memory effects in MOS devices based on Si quantum dots. <i>Materials Science and Engineering C</i> , 2003 , 23, 33-36	8.3	8
109	Improvement of CoSi ₂ thermal stability by cavity formation. <i>Applied Physics Letters</i> , 2001 , 79, 3419-3421	3.4	8
108	Precipitation of As in thermally oxidized ion-implanted Si crystals. <i>Applied Physics Letters</i> , 1998 , 73, 2633-2635	3.4	8
107	Arsenic and boron diffusion in silicon from implanted cobalt silicide layers. <i>Semiconductor Science and Technology</i> , 1995 , 10, 1362-1367	1.8	8
106	Titanium silicide as a diffusion source for phosphorous: precipitation and activation. <i>Applied Surface Science</i> , 1991 , 53, 190-195	6.7	8

105	Realignment of As doped silicon films deposited on silicon substrates. <i>Semiconductor Science and Technology</i> , 1991 , 6, 850-856	1.8	8
104	TiC, Ti, and C as a mixing barrier for Ni-Si ion beam mixing. <i>Applied Physics Letters</i> , 1987 , 50, 177-179	3.4	8
103	Thick sample analysis by ion induced X-rays. <i>Nuclear Instruments & Methods</i> , 1978 , 149, 435-440		8
102	Laser annealing of self-ion damaged silicon. <i>Applied Physics Letters</i> , 1979 , 35, 701-703	3.4	8
101	Multiple scattering justifies depth dependence of critical angles. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1971 , 35, 117-118	2.3	8
100	Nanoscale capacitive behaviour of ion irradiated graphene on silicon oxide substrate. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 907-911	1.3	7
99	Structural relationship of polycrystalline cobalt silicide lines to (001) silicon substrate and their thermal stability. <i>Microelectronic Engineering</i> , 2001 , 55, 163-169	2.5	7
98	Determination of C54 nucleation site density in narrow stripes by sheet resistance measurements and Raman spectroscopy. <i>Microelectronic Engineering</i> , 2000 , 50, 139-145	2.5	7
97	Experimental analysis of high energy boron implantation in silicon. <i>Radiation Effects and Defects in Solids</i> , 1994 , 129, 133-139	0.9	7
96	Realignment of As doped polycrystalline Si films by double step annealing. <i>Applied Physics Letters</i> , 1991 , 59, 2507-2509	3.4	7
95	Concentration dependence and interfacial instabilities during ion beam annealing of arsenic-doped silicon. <i>Applied Physics Letters</i> , 1990 , 56, 24-26	3.4	7
94	Dependence of PtSi Schottky diode electrical behaviour on the platinum film thickness and on the annealing process. <i>Thin Solid Films</i> , 1988 , 161, 13-20	2.2	7
93	Hole mobility in aluminium implanted silicon. <i>Semiconductor Science and Technology</i> , 1997 , 12, 1433-1437	1.8	6
92	In situ sensor for interstitial trapping during Si thermal oxidation using He implantation-induced voids. <i>Applied Physics Letters</i> , 2001 , 79, 3959-3961	3.4	6
91	Rapid thermal processing reliability of titanium silicide implanted with arsenic, boron and phosphorus. <i>Applied Surface Science</i> , 1991 , 53, 377-382	6.7	6
90	Titanium silicide as a diffusion source for arsenic. <i>Journal of Applied Physics</i> , 1990 , 67, 7174-7176	2.5	6
89	Off-axis channeling disorder analysis. <i>Journal of Applied Physics</i> , 1976 , 47, 5206-5213	2.5	6
88	Temperature dependence of planar channeling in transmission experiments. <i>Nuclear Instruments & Methods</i> , 1976 , 132, 169-173		6

87	Influence of scattering on MeV He+ channeling in Si overlaid by amorphous films. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 1971 , 37, 157-158	2.3	6
86	Influence of hydrofluoric acid treatment on electroless deposition of Au clusters. <i>Beilstein Journal of Nanotechnology</i> , 2017 , 8, 183-189	3	5
85	Crystallization properties of Sb-rich GeSbTe alloys by in-situ morphological and electrical analysis. <i>Materials Science in Semiconductor Processing</i> , 2017 , 65, 100-107	4.3	5
84	Radiation pressure excitation and cooling of a cryogenic micro-mechanical systems cavity. <i>Journal of Applied Physics</i> , 2009 , 106, 013108	2.5	5
83	Crystallization of Nanometer Ge ₂ Sb ₂ Te ₅ Amorphous Regions Embedded in the Hexagonal Close Packed Structure. <i>Electrochemical and Solid-State Letters</i> , 2012 , 15, H105		5
82	Interaction and Migration Properties of Ion Beam Induced Point Defects in Crystalline Silicon: Basic Research and Technological Relevance. <i>Defect and Diffusion Forum</i> , 1997 , 153-155, 137-158	0.7	5
81	Electron programming and hole erasing in silicon nanocrystal Flash memories with fin field-effect transistor architecture. <i>Applied Physics Letters</i> , 2008 , 92, 203503	3.4	5
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